

General Description

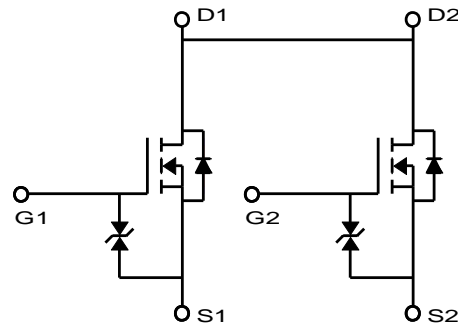
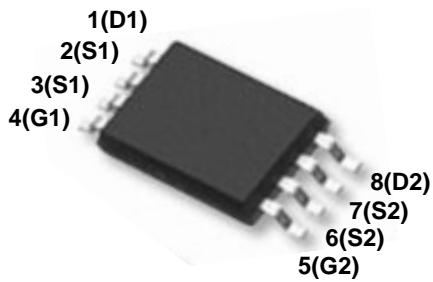
The MDC0531E uses advanced MagnaChip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent reliability. Low $R_{DS(ON)}$ and low gate charge operation with gate voltage as low as 2.5V

Features

- $V_{DS} = 30V$
- $I_D = 8.0A$ @ $V_{GS} = 10V$
- $R_{DS(ON)} < 20m\Omega$ @ $V_{GS} = 10V$
- $R_{DS(ON)} < 23m\Omega$ @ $V_{GS} = 4.5V$

Applications

- Unidirectional or Bi-directional Load Switch
- Lithium-Ion Battery Packs
- Portable Battery Protection Module



Absolute Maximum Ratings ($T_a = 25^\circ C$)

| Characteristics | | Symbol | Rating | Unit |
|--|--------------------|----------------|----------|------------|
| Drain-Source Voltage | | V_{DSS} | 30 | V |
| Gate-Source Voltage | | V_{GSS} | ± 12 | V |
| Continuous Drain Current | $T_C = 25^\circ C$ | I_D | 8 | A |
| | $T_C = 70^\circ C$ | | 6.5 | A |
| Pulsed Drain Current | | I_{DM} | 45 | A |
| Power Dissipation ⁽¹⁾ | $T_A = 25^\circ C$ | P_D | 1.7 | W |
| | $T_A = 70^\circ C$ | | 1.0 | |
| Junction and Storage Temperature Range | | T_J, T_{stg} | -55~150 | $^\circ C$ |

Thermal Characteristics

| Characteristics | Symbol | Rating | Unit |
|--|-----------------|--------|--------------|
| Thermal Resistance, Junction-to-Ambient ⁽¹⁾ | $R_{\theta JA}$ | 75 | $^\circ C/W$ |
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 6 | |

Ordering Information

| Part Number | Temp. Range | Package | Packing | RoHS Status |
|-------------|-------------|---------|-------------|--------------|
| MDC0531ET | -55~150°C | TSSOP-8 | Tube | Halogen Free |
| MDC0531ER | -55~150°C | TSSOP-8 | Tape & Reel | Halogen Free |

Electrical Characteristics (Ta =25°C)

| Characteristics | Symbol | Test Condition | Min | Typ | Max | Unit |
|--|--------------|---|-----|------|-----|------------|
| Static Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $I_D = 250\mu A, V_{GS} = 0V$ | 30 | - | - | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 0.6 | 0.85 | 1.5 | |
| Drain Cut-Off Current | I_{DSS} | $V_{DS} = 24V, V_{GS} = 0V$ | - | - | 1 | μA |
| Gate Leakage Current | I_{GSS} | $V_{GS} = \pm 10V, V_{DS} = 0V$ | - | - | 10 | μA |
| Drain-Source ON Resistance | $R_{DS(on)}$ | $V_{GS} = 10V, I_D = 5.0A$ | - | 17 | 20 | m Ω |
| | | $V_{GS} = 4.5V, I_D = 5.0A$ | - | 19 | 23 | |
| | | $V_{GS} = 2.5V, I_D = 3.0A$ | - | 24 | - | |
| Forward Transconductance | g_{fs} | $V_{DS} = 5V, I_D = 7A$ | - | 33 | - | S |
| Dynamic Characteristics | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = 15V, I_D = 5A, V_{GS} = 4.5V$ | - | 10.7 | - | nC |
| Gate-Source Charge | Q_{gs} | | - | 2.1 | - | |
| Gate-Drain Charge | Q_{gd} | | - | 4.3 | - | |
| Input Capacitance | C_{iss} | $V_{DS} = 15V, V_{GS} = 0V, f = 1.0MHz$ | - | 870 | - | pF |
| Reverse Transfer Capacitance | C_{riss} | | - | 105 | - | |
| Output Capacitance | C_{oss} | | - | 115 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{GS} = 10V, V_{DS} = 15V, R_L = 1.25\Omega, R_G = 3\Omega$ | - | 3.5 | - | ns |
| Rise Time | t_r | | - | 11 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 27 | - | |
| Fall Time | t_f | | - | 6.5 | - | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Source-Drain Diode Forward Voltage | V_{SD} | $I_S = 1A, V_{GS} = 0V$ | 0.5 | 0.71 | 0.9 | V |
| Source-Drain Diode Forward Voltage | V_{SD} | $I_S = 4.5A, V_{GS} = 0V$ | - | - | 1.0 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = 11.6A, di/dt = 100A/\mu s$ | - | 24 | - | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | - | 13 | - | nC |

Note :

1. Surface mounted FR-4 board with 2oz. Copper.

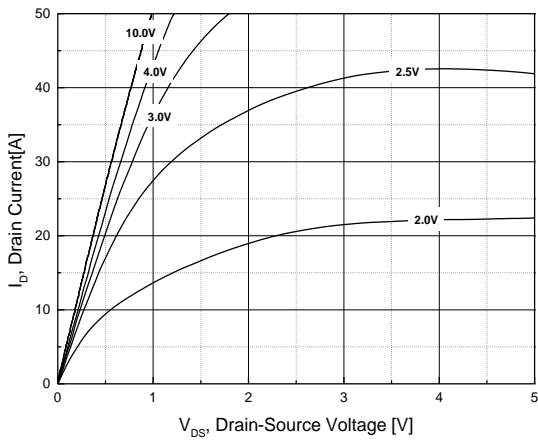


Fig.1 On-Region Characteristics

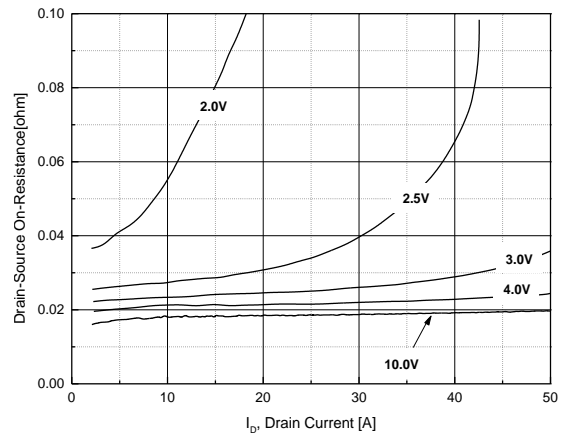


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

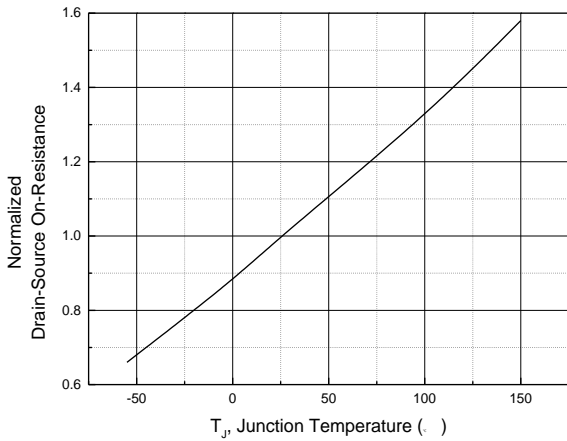


Fig.3 On-Resistance Variation with Temperature

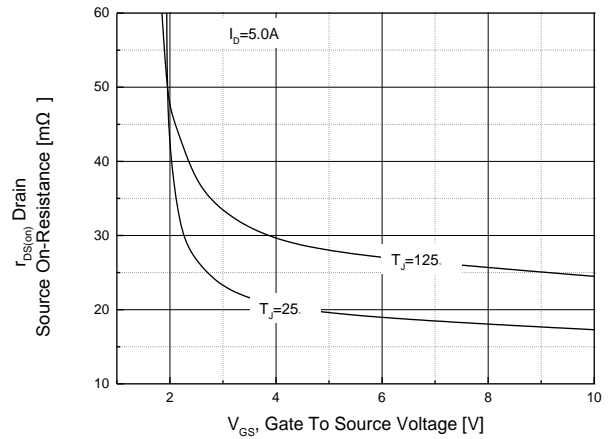


Fig.4 On-Resistance Variation with Gate to Source Voltage

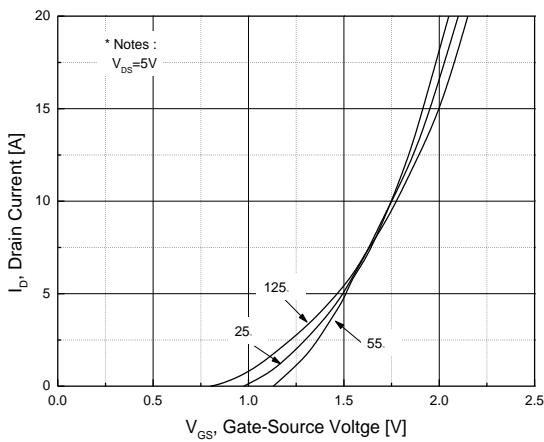


Fig.5 Transfer Characteristics

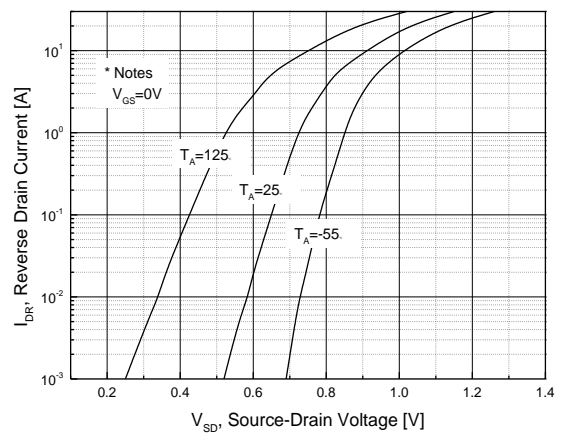


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

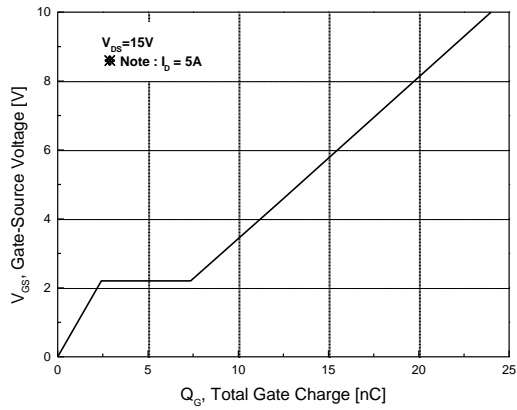


Fig.7 Gate Charge Characteristics

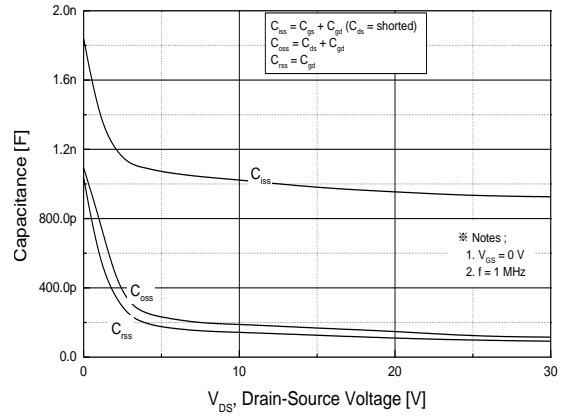


Fig.8 Capacitance Characteristics

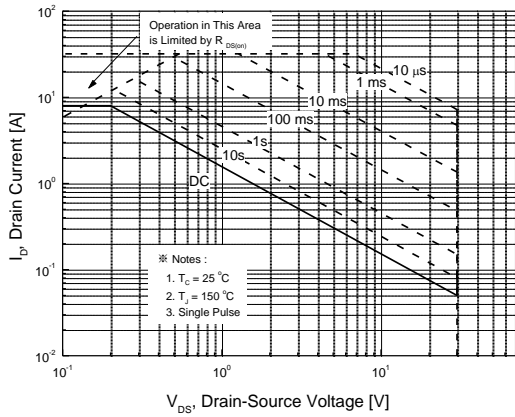


Fig.9 Maximum Safe Operating Area

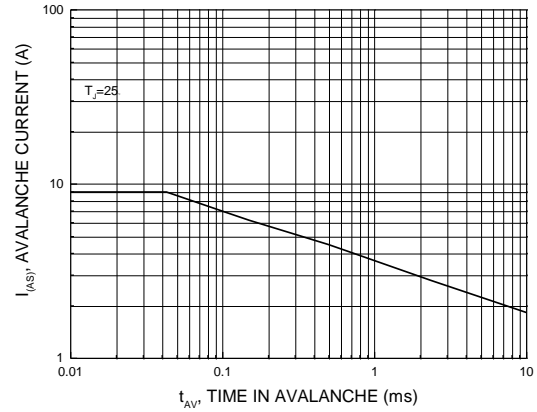


Fig.10 Unclamped Inductive Switching Capability

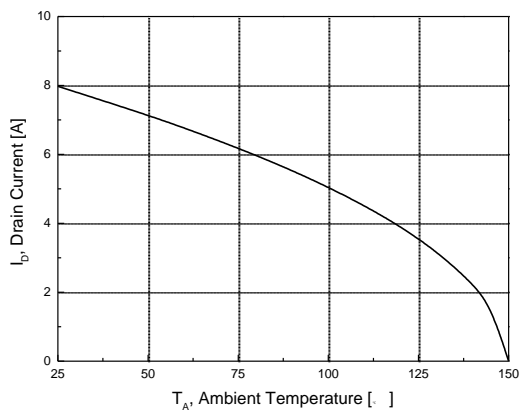


Fig.11 Maximum Drain Current vs. Case Temperature

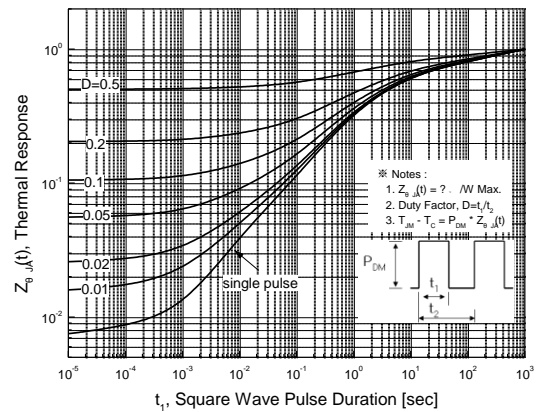


Fig.12 Transient Thermal Response Curve

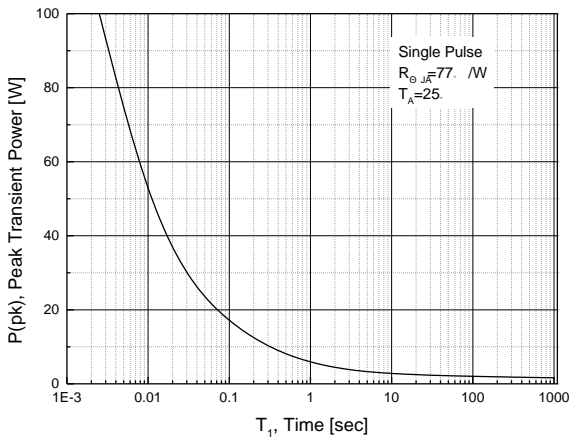


Fig13. Single Pulse Maximum Power Dissipation

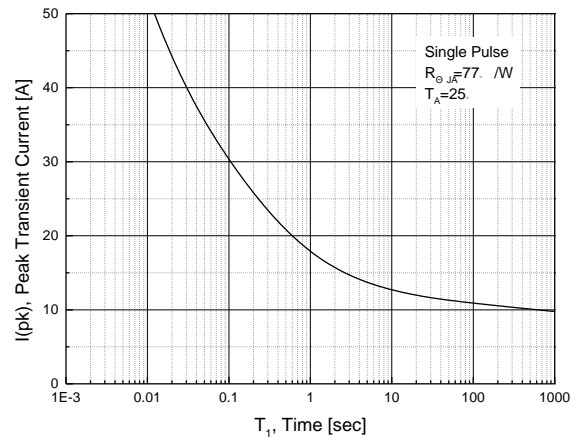
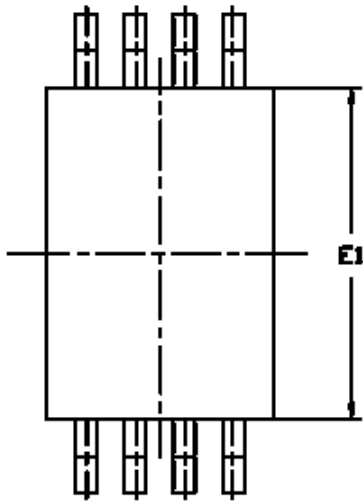


Fig14. Single Pulse Maximum Peak Current

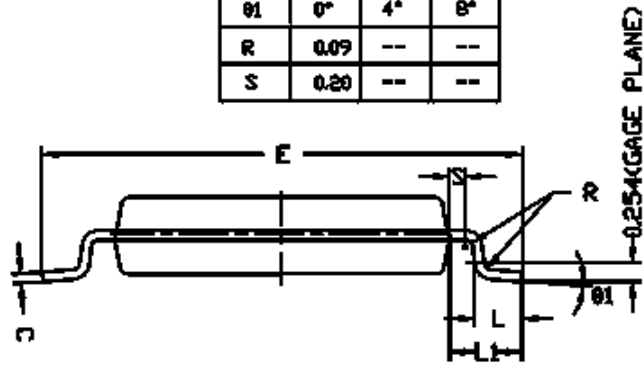
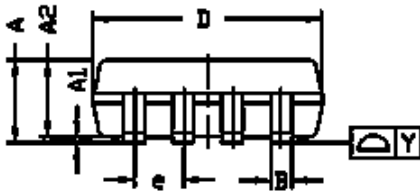
Physical Dimension

TSSOP, 8 Leads

Dimensions are in millimeters, unless otherwise specified



| DIM. | MILLIMETERS | | |
|------|-------------|-------|------|
| | MIN. | NOM. | MAX. |
| A | 1.05 | 1.10 | 1.20 |
| A(1) | 0.05 | 0.10 | 0.15 |
| A(2) | 0.99 | 1.02 | 1.05 |
| B | 0.19 | 0.25 | 0.30 |
| C | -- | 0.127 | -- |
| D | 2.90 | 3.00 | 3.10 |
| E | 6.20 | 6.40 | 6.60 |
| E1 | 4.30 | 4.40 | 4.50 |
| φ | 0.65BSC | | |
| L | 0.45 | 0.60 | 0.75 |
| L1 | 0.90 | 1.00 | 1.10 |
| Y | -- | -- | 0.10 |
| θ1 | 0° | 4° | 8° |
| R | 0.09 | -- | -- |
| S | 0.20 | -- | -- |



0.254(GAGE PLANE)

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